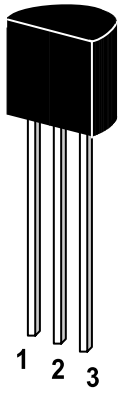
ST 2SA933

PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and S, according to its DC current gain. As complementary type the NPN transistor ST 2SC945 is recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	125	^{O}C
Storage Temperature Range	T_S	-65 to +150	^{O}C

ST 2SA933

Characteristics at T_{amb}=25 ^{O}C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE}$=6V, $-I_C$=1mA					
Current Gain Group O	h_{FE}	120	-	270	-
Y	h_{FE}	180	-	390	-
S	h_{FE}	270	-	560	-
Collector Base Breakdown Voltage					
at $-I_C$=50μA	$-V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage					
at $-I_C$=1mA	$-V_{(BR)CEO}$	40	-	-	V
Emitter Base Breakdown Voltage					
at $-I_E$=50μA	$-V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current					
at $-V_{CB}$=30V	$-I_{CBO}$	-	-	0.5	μA
Emitter Cutoff Current					
at $-V_{EB}$=4V	$-I_{EBO}$	-	-	0.5	μA
Collector Saturation Voltage					
at $-I_C$=50mA, $-I_B$=5mA	$-V_{CE(sat)}$	-	0.1	0.5	V
Gain Bandwidth Product					
at $-V_{CE}$=12V, $-I_C$=2mA	f_T	-	140	-	MHz
Output Capacitance					
at $-V_{CB}$=12V, f=1MHz	C_{OB}	-	4	5	pF